

Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- NPN Complements to BCX54,BCX55,BCX56
- Low Voltage
- High Current

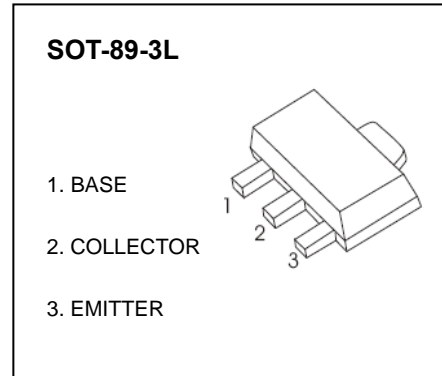
APPLICATIONS

- Medium Power General Purposes
- Driver Stages of Audio Amplifiers

MARKING:BCX51:AA, BCX51-10:AC, BCX51-16:AD
BCX52:AE, BCX52-10:AG, BCX52-16:AM
BCX53:A H, BCX53-10:AK, BCX53-16:AL

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BCX51	-45
		BCX52	-60
		BCX53	-100
V_{CEO}	Collector-Emitter Voltage	BCX51	-45
		BCX52	-60
		BCX53	-80
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$





ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	BCX51	-45		V
			BCX52	-60		
			BCX53	-100		
Collector-emitter breakdown voltage	V _{(BR)CEO*}	I _C =-10mA, I _B =0	BCX51	-45		V
			BCX52	-60		
			BCX53	-80		
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)*}	V _{CE} =-2V, I _C =-5mA	63			
	h _{FE(2)*}	V _{CE} =-2V, I _C =-150mA	63		250	
	h _{FE(3)*}	V _{CE} =-2V, I _C =-0.5A	40			
Collector-emitter saturation voltage	V _{CE(sat)*}	I _C =-0.5A, I _B =-50mA			-0.5	V
Base-emitter voltage	V _{BE*}	V _{CE} =-2V, I _C =-0.5A			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz		50		MHz

* Pulse Test

CLASSIFICATION OF h_{FE(2)}

RANK	BCX51 BCX52 BCX53	BCX51-10 BCX52-10 BCX53-10	BCX51-16 BCX52-16 BCX53-16
RANGE	63-250	63-160	100-250



Typical Characteristics

